

## Product Overview

### NGTD17T65F2: IGBT 600V 40A FS2 bare die

For complete documentation, see the data sheet.

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop II Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss.

### Features

- Extremely Efficient Trench with Field Stop Technology
- $T_{Jmax} = 175^{\circ}C$
- Optimized for High Speed Switching
- 5  $\mu s$  Short Circuit Capability
- These are Pb-Free Devices

### Applications

- Solar Inverter
- Uninterruptible Power Inverter Supplies (UPS)
- Welding

### Part Electrical Specifications

Product	Compliance	Status	$V_{ES}^{(BR)C}$ Typ (V)	$I_C$ Max (A)	$V_{GE}^{(sa)}$ Typ (V)	$V_F$ Typ (V)	$E_{off}$ Typ (mJ)	$E_{on}$ Typ (mJ)	$T_{rr}$ Typ (ns)	$I_{rr}$ Typ (A)	Gate Charge Typ (nC)	Short Circuit Withs tand ( $\mu s$ )	$E_{AS}$ Typ (mJ)	$P_D$ Max (W)	Co- Pack aged Diode	Pack age Type
NGTD17T65F2SWK	Pb-free	Active	650	-	1.7	-	-	-	-	-	-	5	-	-	-	
	Halide free															
NGTD17T65F2WP	Pb-free	Active	650	-	1.7	-	-	-	-	-	-	5	-	-	-	
	Halide free															

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com).

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